

# **HL61C** series Low Power Voltage Detector

#### **Features**

- Lowpowerconsumption
- Low temperature coefficient
- Built-in hysteresis characteristic
- High input voltage (up to 8V)
- Output voltage accuracy:

 $\pm 2\%$ @VDET $\geqslant$ 2.5mV

 $\pm$ 50mV@VDET<2.5mV

SOT23-3 and SOT23 package

### **Applications**

- Battery checkers
- Level selectors
- Power failure detectors
- Microcomputer reset
- Battery memory backup
- Non-volatile RAM signal storage protectors

### **General Description**

terminal low power voltage detectors implemented in CMOS technology. Each voltage detector in the series detects a particular fixed voltage ranging from 0.9V to 5.0V. The voltage detectors consist of detectors, these devices can be used with external a high-precision and low power consumption components to detect user specified threshold standard voltage source as well as a comparator, voltages.

The HL61C series devices are a set of three hysteresis circuit, and an output driver (CMOS inverter or NMOS open drain). CMOS technology ensures low power consumption.

Although designed primarily as fixed voltage

#### **Selection Table**

Part No.	Det. Voltage	Hys. Width	Output	Tolerance	Package
HL61CC0902MR	0.9V	4%	CMOS	$\pm 50 \text{mV}$	
HL61CN0902MR	0.9V	4%	NMOS	$\pm 50 \mathrm{mV}$	
HL61CC1002MR	1.0V	4%	CMOS	±50mV	
HL61CN1002MR	1.0V	4%	NMOS	$\pm 50 \mathrm{mV}$	
	•••		•••		
HL61CC2402MR	2.4V	4%	CMOS	$\pm 50 \text{mV}$	SOT23-3
HL61CN2402MR	2.4V	4%	NMOS	$\pm 50 \text{mV}$	SOT23
HL61CC2502MR	2.5V	4%	CMOS	±2%	
HL61CN2502MR	2.5V	4%	NMOS	<u>+2</u> %	
•••	•••	• • •	•••	<u>+2</u> %	
HL61CC5002MR	5.0V	4%	CMOS	<u>+2</u> %	
HL61CN5002MR	5.0V	4%	NMOS	<u>+2</u> %	

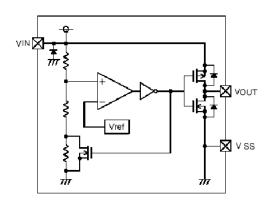
## **Order Information**

HL61C1234567

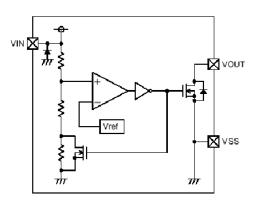
Designator	Symbol	Description
(1)	С	CMOS output
(1)	N	NMOS output
23	VOUT	Output Voltage(0.9~5.0V)
45	02	Standard
6	M	Package:SOT23-3
0	N	Package:SOT23
7	R	RoHS/Pb Free
	G	Halogen Free

## **Block Diagram**

## (1) CMOS Output

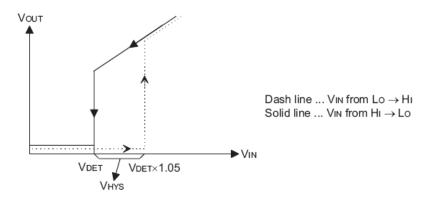


### (2) N-ch Open Drain Output

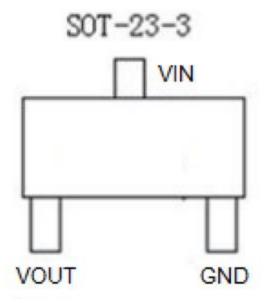


## **Output Table & Curve**

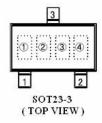
$V_{DD}$	$V_{DD}>V_{DET}(+)$	V <sub>DD</sub> ≪V <sub>DET</sub> (-)
Vout	Hi-Z	V <sub>SS</sub>



## Pin Assignment



## Marking Rule



# ① Represents integer of detect voltage and CMOS Output

MARK	CONFIGURATION	VOLTAGE (V)
А	CMOS	0.X
В	CMOS	1.X
С	CMOS	2.X
D	CMOS	3.X
Е	CMOS	4.X
F	CMOS	5.X
H	CMOS	6.X

#### N-Channel Open Drain Output

MARK	CONFIGURATION	VOLTAGE (V)
K	N-ch	0.X
L	N-ch	1.X
М	N-ch	2.X
N	N-ch	3.X
Р	N-ch	4.X
R	N-ch	5.X
S	N-ch	6.X

#### @Represents decimal number of detect voltage

MARK	VOLTAGE (V)	MARK	VOLTAGE (V)
0	X.0	5	X.5
1	X.1	6	X.6
2	X.2	7	X.7
3	X.3	8	X.8
4	X.4	9	X.9

#### ③ Represents accuracy

MARK	ACCURACY
3	2%
1	1%

(4) Represents production lot number Based on the internal standard. (G, I, J, O, Q, W excepted)

### **Absolute Maximum Ratings**

Supply Voltage ......-0.3 V to 8 V Storage Temperature .....-50  $^{\circ}$ C to 125  $^{\circ}$ C Operating Temperature .....-40  $^{\circ}$ C to 85  $^{\circ}$ C

Note: These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

### **Thermal Information**

Symbol	Parameter	Package	Max.	Unit
θ ЈА	Thermal Resistance (Junction to Ambient) (Assume no ambient airflow, no heat sink)	SOT23-3	500	°C/W
P <sub>D</sub>	Power Dissipation	SOT23-3	0.20	W

Note:  $P_D$  is measured at  $Ta = 25 ^{\circ}C$ 

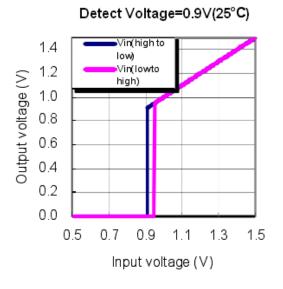
#### **Electrical Characteristics**

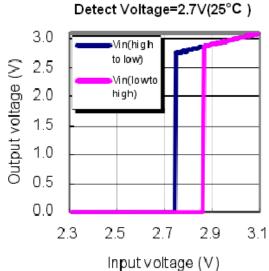
 $V_{DF}=0.8V\sim5.0V$  Ta=25 °C

Symbol	Parameter	Te	est Conditions	Min.	Тур.	Max.	Unit
	Datastian Valtaga	V	<sub>DF</sub> =0.9V~2.4V	V <sub>DET</sub> -0.05	$V_{DET}$	V <sub>DET</sub> +0.05	V
V <sub>DET</sub>	Detection Voltage	V	<sub>DF</sub> =2.5V~5.0V	V <sub>DET</sub> *0.98	$V_{DET}$	V <sub>DET</sub> *1.02	V
V <sub>HYS</sub>	Hysteresis Width		-	0.02*V <sub>DET</sub>	0.05*V <sub>DET</sub>	0.10*V <sub>DET</sub>	V
		Vin=1.5V		-	0.7	2.3	μА
		Vin=2.0V		-	0.8	2.7	
$I_{DD}$	Operating Current	Vin=3.0V		-	0.9	3.0	
		Vin=4.0V		-	1.0	3.2	
			Vin=5.0V	-	1.1	3.6	
$V_{DD}$	Operating Voltage	ı	-	0.7	•	10	>
l <sub>OL</sub>	Output Sink Current	2V	V <sub>OUT</sub> =0.2V	0.5	1	-	mA
$\frac{\Delta V_{DET}}{V_{DF}\Delta T_a}$	Temperature Coefficient	-	-25℃ <ta<125℃< td=""><td>-</td><td>±100</td><td>-</td><td>ppm/°C</td></ta<125℃<>	-	±100	-	ppm/°C

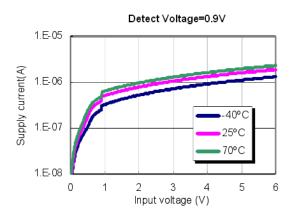
## **Typical Performance Characteristics**

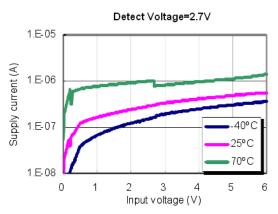
## (1) Output Voltage vs Input voltage





(2) Supply Current vs. Input Voltage



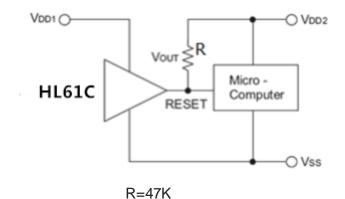


## **Application Circuits**

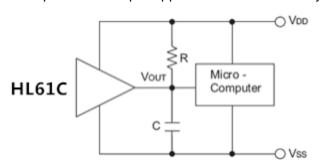
### **Microcomputer Reset Circuit**

Normally a reset circuit is required to protect the microcomputer system from malfunctions due to power line interruptions. The following examples show how different output configurations perform a reset function in various systems.

NMOS open drain output application for separate power supply

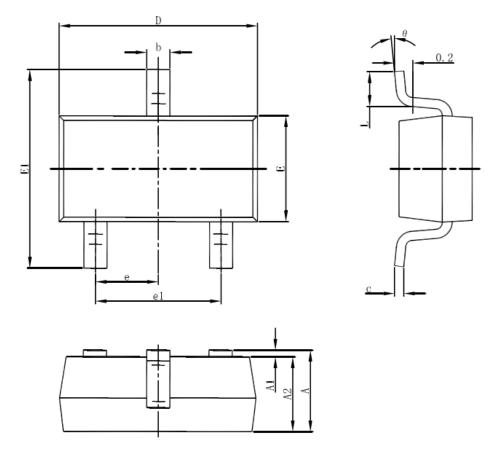


NMOS open drain output application with R-C delay



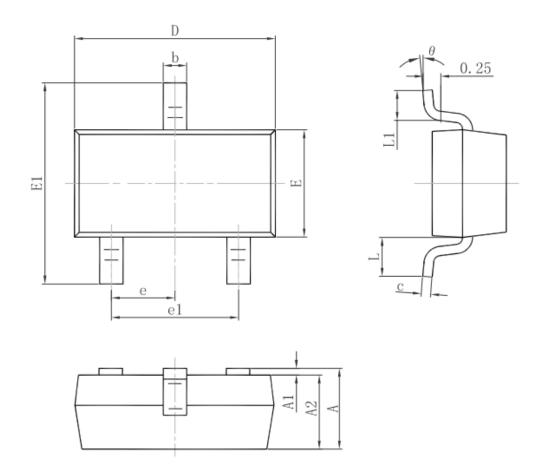
# Package Information

# 3-pin SOT23-3 Outline Dimensions



Symbol	Dimensions In	n Millimeters	Dimensions	In Inches	
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	0.950(BSC) 0.037		(BSC)	
e1	1.800	2.000	0.071	0.079	
Ĺ	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

## 3-pin SOT23 Outline Dimensions



Symbol	Dimensions	In Millimeters	Dimension	s In Inches
	Min.	Max.	Min.	Max.
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP.		0.037	TYP.
e1	1.800	2.000	0.071	0.079
L	0.550	0 REF. 0.022 REF.		REF.
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°